



PXT3904

NPN Silicon Epitaxial Planar Transistor

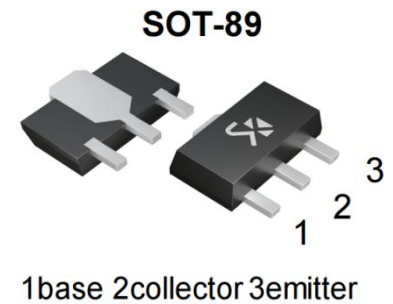
Feature

- Low current
- Low voltage

Marking:1A

Maximum Ratings($T_A=25^{\circ}\text{C}$, unless otherwise noted.)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current Continuous	I_C	200	mA
Collector Power Dissipation	P_C	500	mW
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^{\circ}\text{C}$



Electrical Characteristics($T_A=25^{\circ}\text{C}$, unless otherwise noted.)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=10\mu\text{A}, I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}, I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=30\text{V}, I_E=0$			50	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=6\text{V}, I_C=0$			50	nA
Collector cut-off current	I_{CEX}	$V_{CE}=30\text{V}, V_{BE(off)}=3\text{V}$			50	nA
DC current gain	h_{FE}	$V_{CE}=1\text{V}, I_C=0.1\text{mA}$	60			
		$V_{CE}=1\text{V}, I_C=1\text{mA}$	80			
		$V_{CE}=1\text{V}, I_C=10\text{mA}$	100		300	
		$V_{CE}=1\text{V}, I_C=50\text{mA}$	60			
		$V_{CE}=1\text{V}, I_C=100\text{mA}$	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.2	V
		$I_C=50\text{mA}, I_B=5\text{mA}$			0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.85	V
		$I_C=50\text{mA}, I_B=5\text{mA}$			0.95	V
Transition frequency	f_T	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	300			MHz



Typical Characteristics

Fig. 1 - Static Characteristics

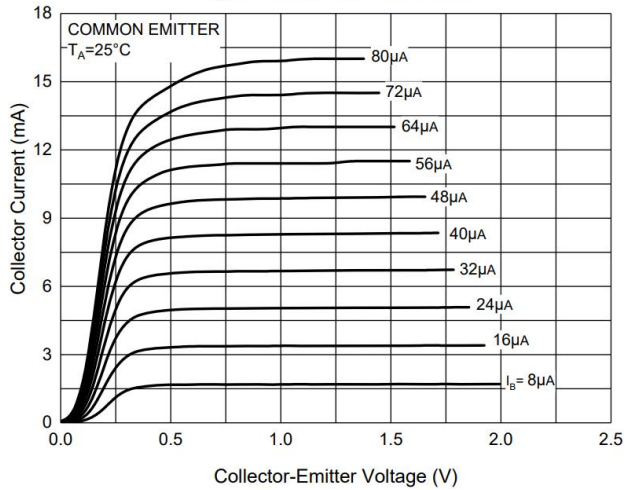


Fig. 2 - DC Current Gain Characteristics

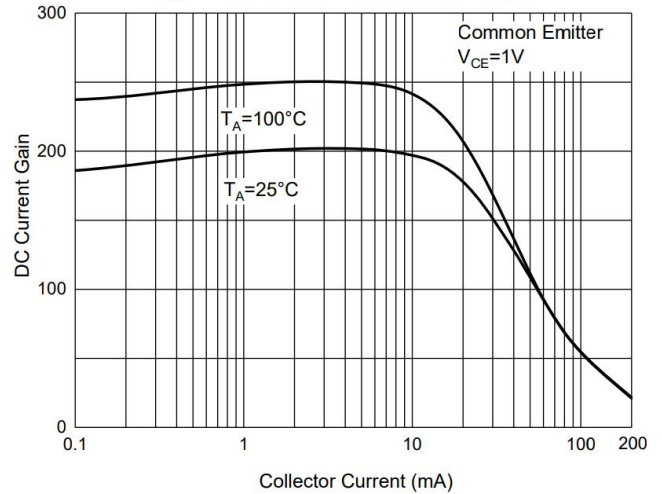


Fig. 3 - Collector-Emitter Saturation Voltage Characteristics

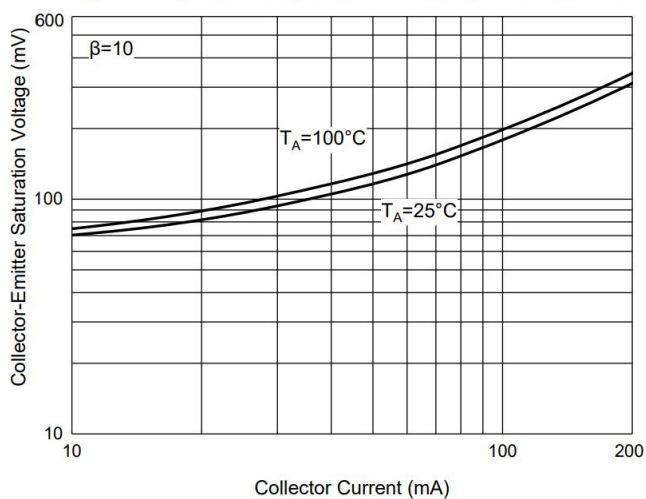


Fig. 4 - Base-Emitter Saturation Voltage Characteristics

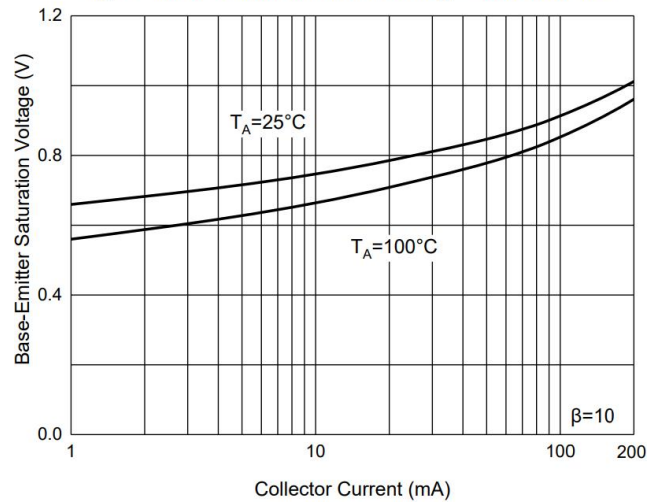


Fig. 5 - Base-Emitter Voltage Characteristics

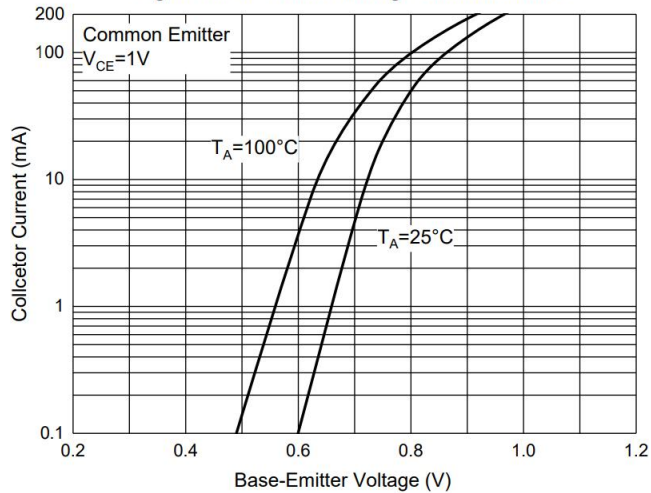
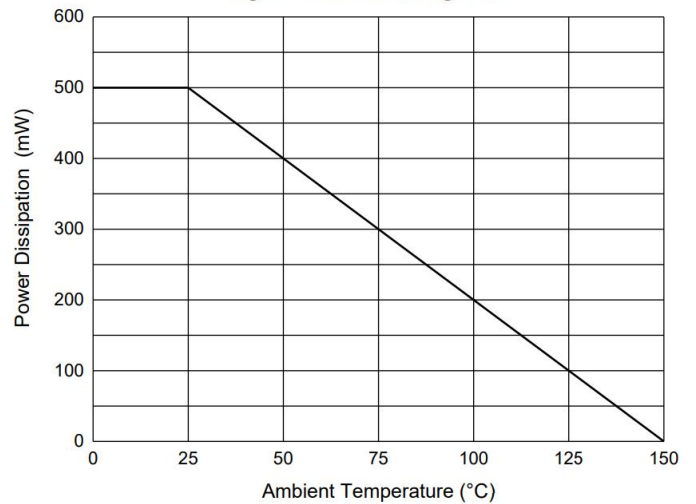


Fig. 6 - Power Derating Curve

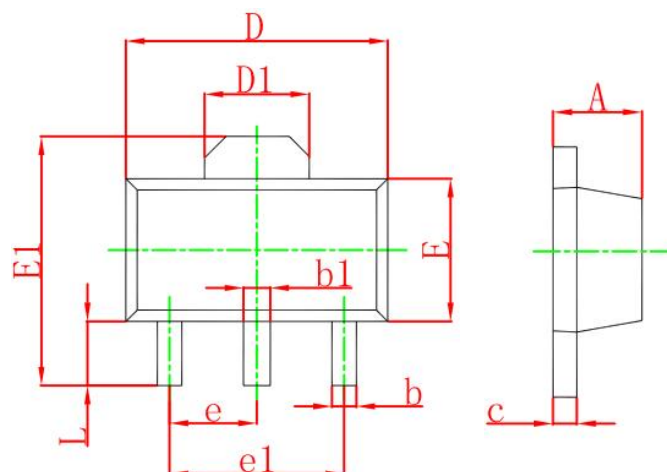




Package Information

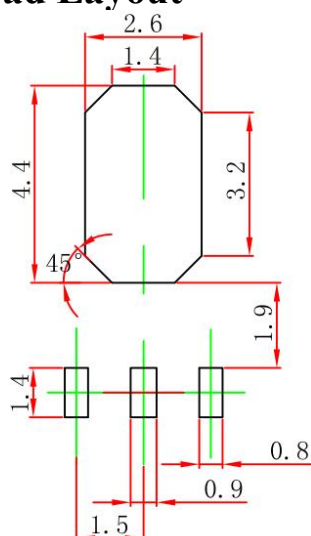
SOT-89

Dimensions in mm



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047

Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters
2. General tolerance: $\pm 0.05\text{mm}$
3. The pad layout is for reference purposes only



Shikues Disclaimer

1.Accuracy of Information and Right to Modify

The information provided in this document is for reference only. Shikues reserves the right to make changes to this document and to the specifications of the products described herein at any time, without prior notice, for the purpose of improving reliability, function, design, or for any other reason. It is the customer's responsibility to obtain and verify the latest product information and specifications before making any final design, procurement, or usage decisions.

2.No Warranty

Shikues makes no express or implied warranties, representations, or guarantees regarding the suitability of its products for any particular purpose.

Shikues assumes no liability for any assistance provided or for the design of customer products. All products are supplied "as is."

3.Intended Use and Limitation of Liability

The products described in this document are intended for use in general-purpose electronic devices. They are neither designed nor tested nor authorized for use in transportation equipment or applications requiring high reliability. Unless expressly authorized in writing by Shikues, these products must not be used as critical components in life-support systems or any applications where failure could directly pose a risk to human life (including, but not limited to, medical devices, transportation systems, aerospace equipment, nuclear facilities, and safety-critical systems).

Shikues assumes no responsibility or liability for any consequences arising from the use of its products in unauthorized or unintended applications.

Neither Shikues nor its representatives shall be held liable for any resulting damages.

4.Intellectual Property

This document does not grant any express or implied license—whether by estoppel, implication, or otherwise—to use any intellectual property rights of Shikues.